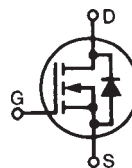


PolarHV™ HiPerFET IXFB 60N80P

Power MOSFET

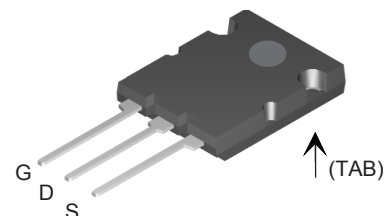
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

$$\begin{aligned} V_{DSS} &= 800 \text{ V} \\ I_{D25} &= 60 \text{ A} \\ R_{DS(on)} &\leq 140 \text{ m}\Omega \\ t_{rr} &\leq 250 \text{ ns} \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	800	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	60	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	150	A
I_{AR}	$T_C = 25^\circ\text{C}$	30	A
E_{AR}	$T_C = 25^\circ\text{C}$	100	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	1250	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
F_C	Mounting force	30..120/7.5...2.7	N/lb
Weight		10	g

PLUS264™ (IXFB)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect

Advantages

- Plus 264™ package for clip or spring
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 3 \text{ mA}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			25 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			3000 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$, Note 1			140 $\text{m}\Omega$

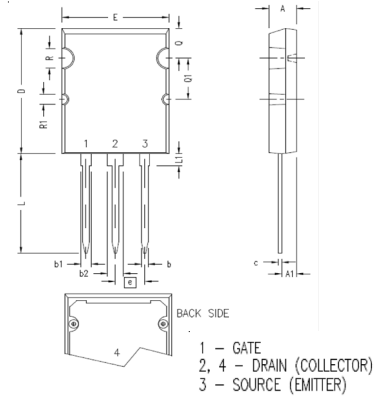
Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20 V; I _D = 0.5 I _{D25} , Note 1	35	67	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	1200	18	nF
C_{oss}				pF
C_{rss}			44	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 1 Ω (External)	110	36	ns
t_r			29	ns
t_{d(off)}				ns
t_f			26	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}	78	250	nC
Q_{gs}			90	nC
Q_{gd}				nC
R_{thJC}		0.13	0.10 °C/W	
R_{thCS}			°C/W	

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	V _{GS} = 0 V			60 A
I_{SM}	Repetitive			150 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5 V
t_{rr}	I _F = 25A, -di/dt = 100 A/μs V _R = 100V	6.0	0.6	250 ns
Q_{RM}				μC
I_{RM}				A

Notes:

1. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %

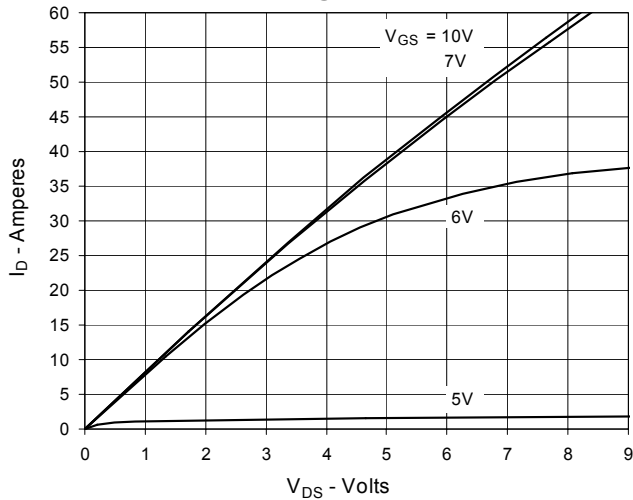
PLUS264™ (IXFB) Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

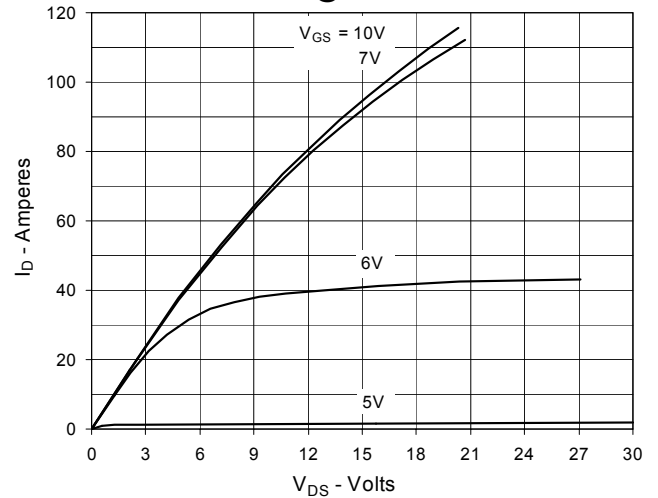
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585
 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

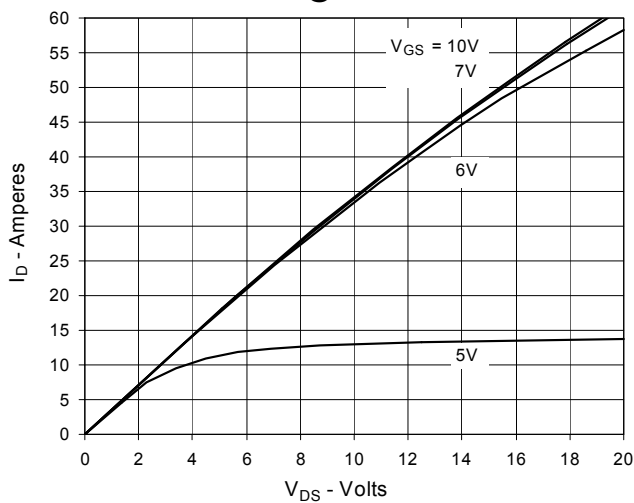
**Fig. 1. Output Characteristics
@ 25°C**



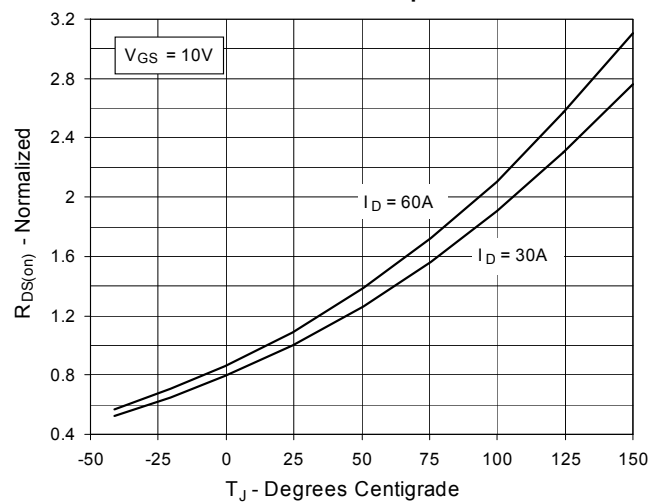
**Fig. 2. Extended Output Characteristics
@ 25°C**



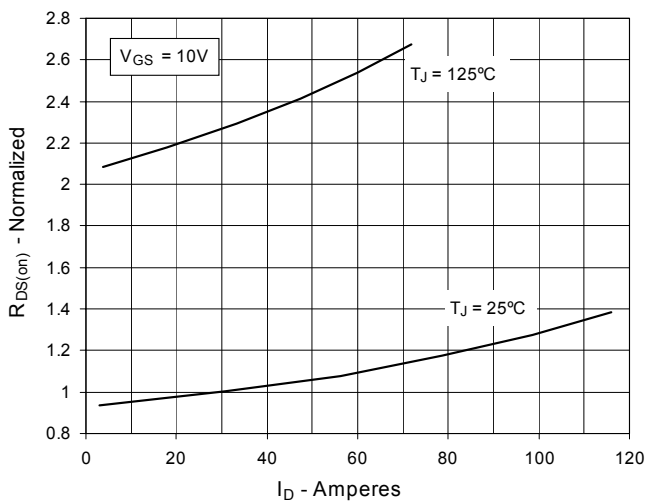
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 30A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 30A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

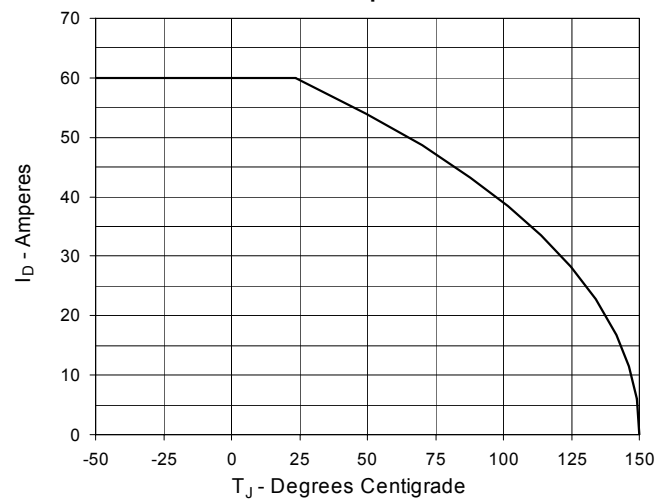


Fig. 7. Input Admittance

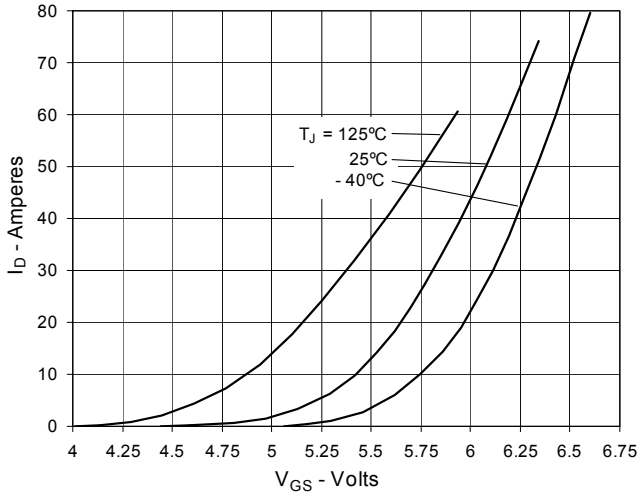


Fig. 8. Transconductance

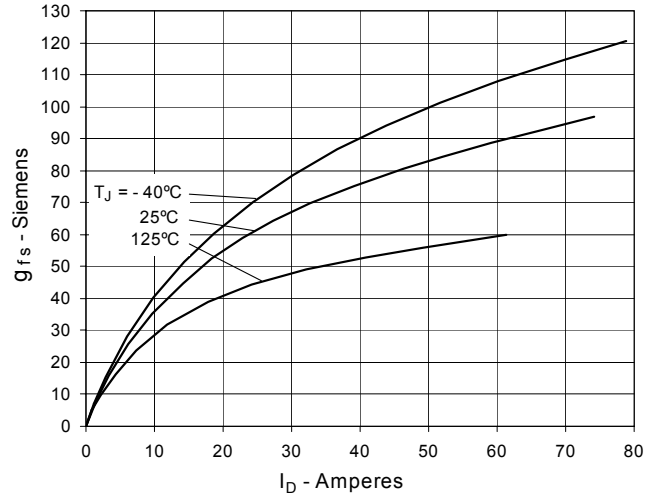


Fig. 9. Forward Voltage Drop of Intrinsic Diode

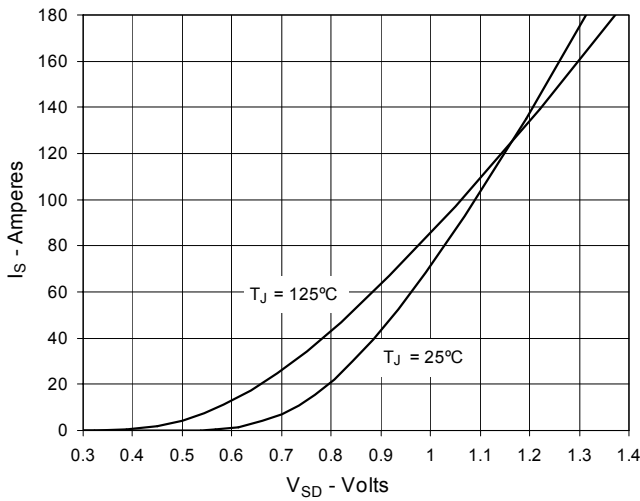


Fig. 10. Gate Charge

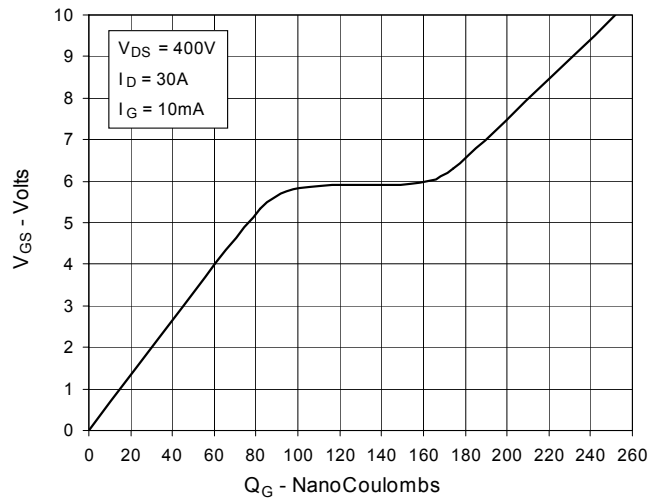


Fig. 11. Capacitance

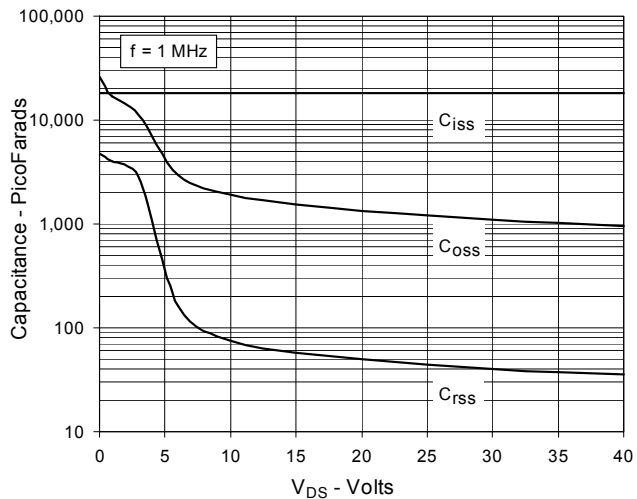
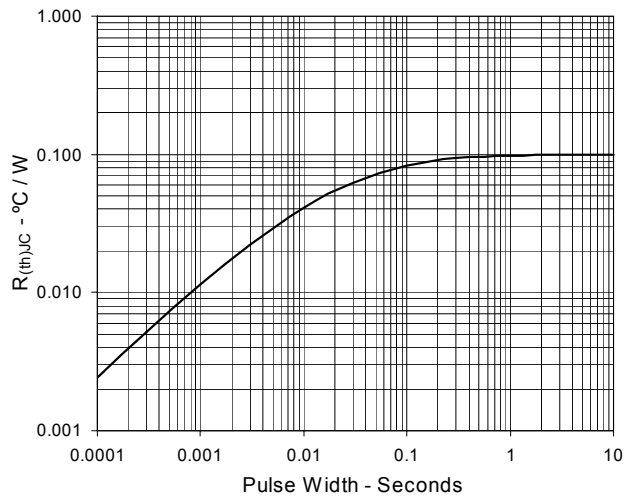


Fig. 12. Maximum Transient Thermal Resistance





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